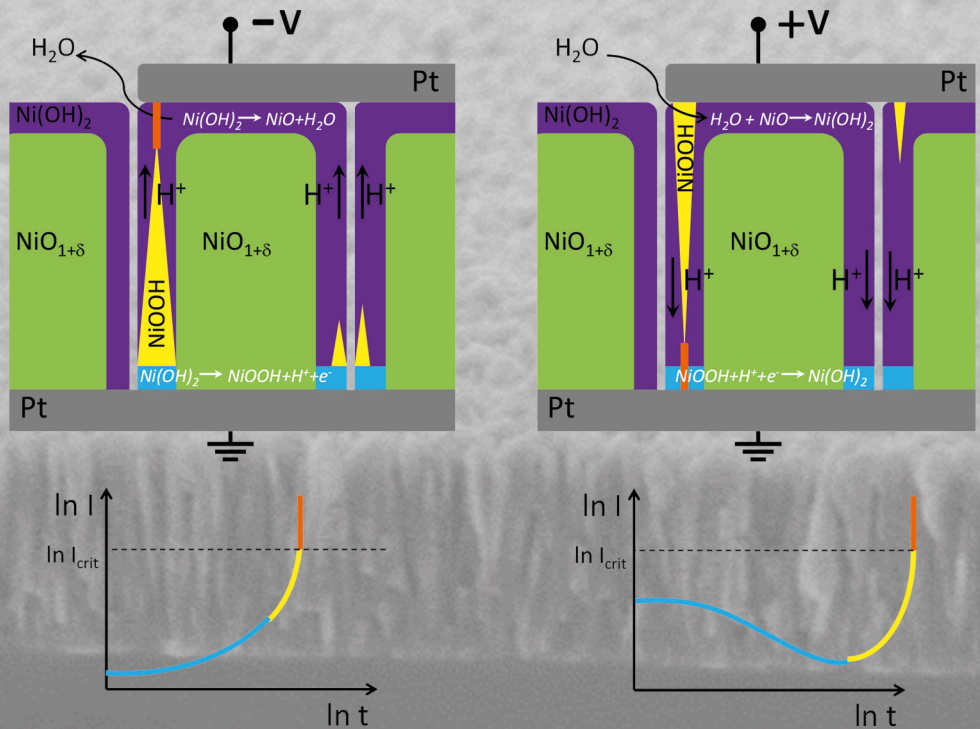


Study on the electroforming and resistive switching behaviour of nickel oxide thin films for non-volatile memory applications

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